KSF260N10S

100V N-Channel MOSFET

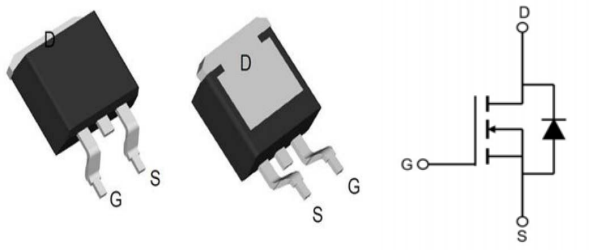
General Description

The KSF260N10S is uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Product Summary

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)
100	2.4 at V_{GS} = 10 V	260

TO-263 Pin Configuration



Features

- Low RDS(ON)
- Low Gate Charger
- Trench Power technology

Applications

- BMS battery protection
- Synchronous Rectifiers in DC/DC
- Industrial and Motor Drive applications

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±25	V
I_D	Drain Current – Continuous (T_C=25℃)	260	A
	Drain Current – Continuous (T_C=100℃)	150	A
I_{DM}	Drain Current – Pulsed[1]	780	A
P_D	Power Dissipation (T_C=25℃)	350	W
	Power Dissipation (T_C=100℃)	2.5	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.65	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=50V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±25V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=15A	---	2.4	3.2	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
gfs	Forward Transconductance	V_{DS}=10V , I_S=18A	---	60	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=10A	---	165	---	nC
Q_{gs}	Gate-Source Charge		---	43	---	
Q_{gd}	Gate-Drain Charge		---	38	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=50V,R_L=2.0Ω V_{GS}=10V,R_G=3.0Ω	---	32	---	ns
T_r	Rise Time		---	119	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time		---	143	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , F=1MHz	---	9312	---	pF
C_{oss}	Output Capacitance		---	1565	---	
C_{rss}	Reverse Transfer Capacitance		---	83	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	260	A
I_{SM}	Pulsed Source Current		---	---	760	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

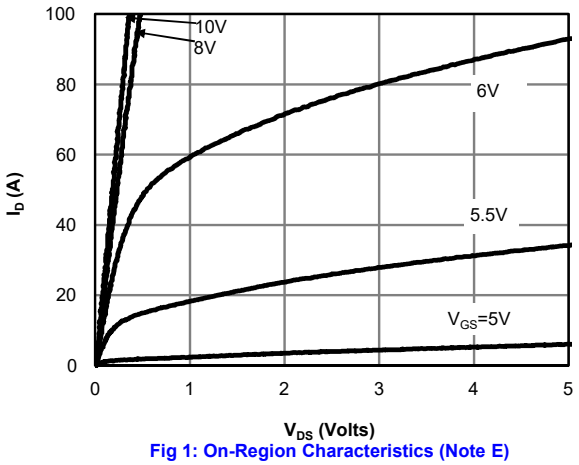


Fig 1: On-Region Characteristics (Note E)

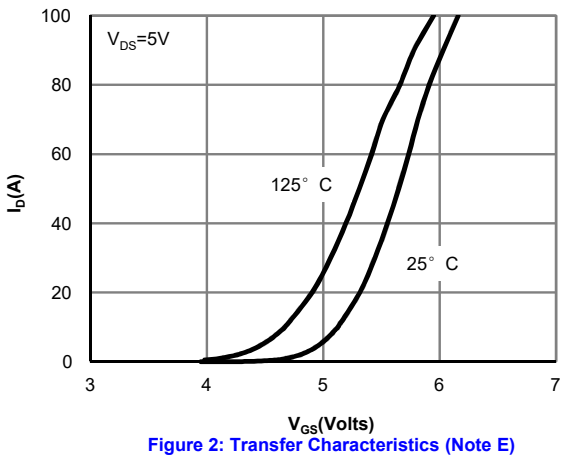


Figure 2: Transfer Characteristics (Note E)

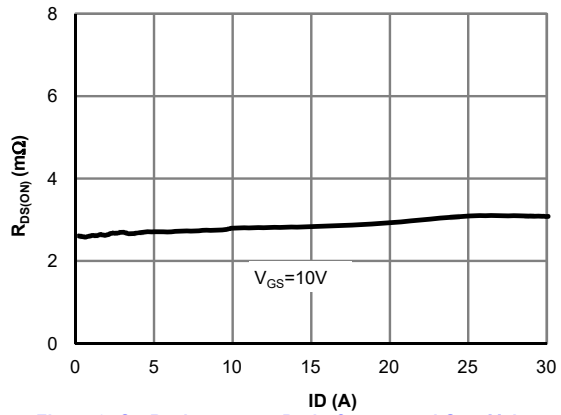


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

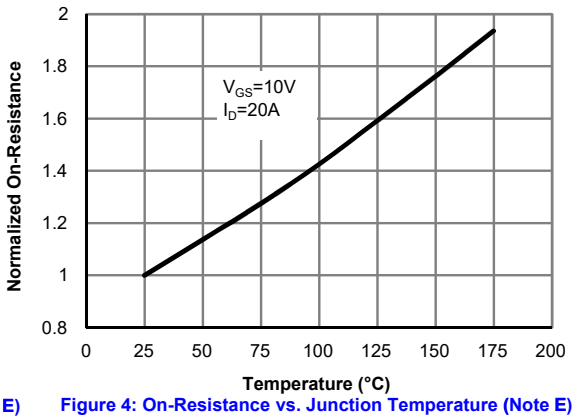


Figure 4: On-Resistance vs. Junction Temperature (Note E)

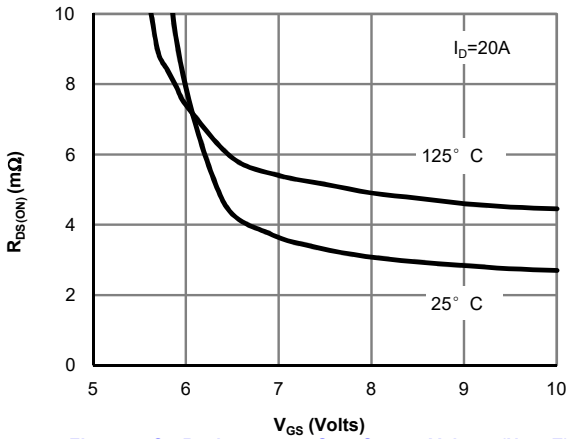


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

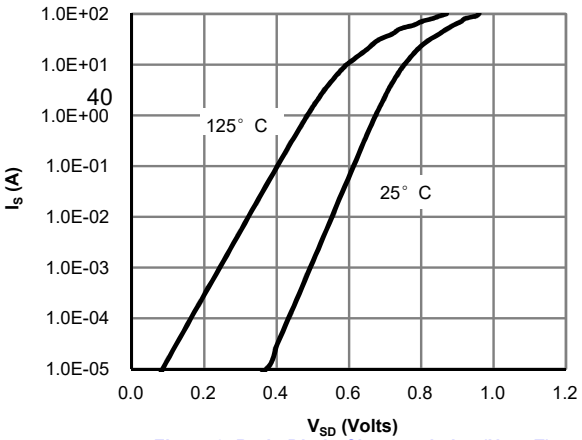


Figure 6: Body-Diode Characteristics (Note E)

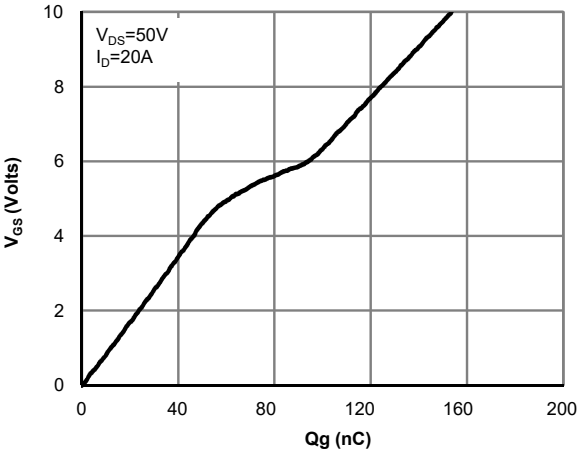


Figure 7: Gate-Charge Characteristics

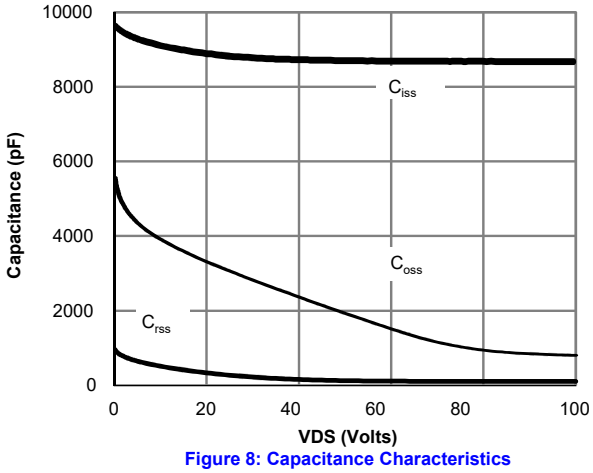


Figure 8: Capacitance Characteristics

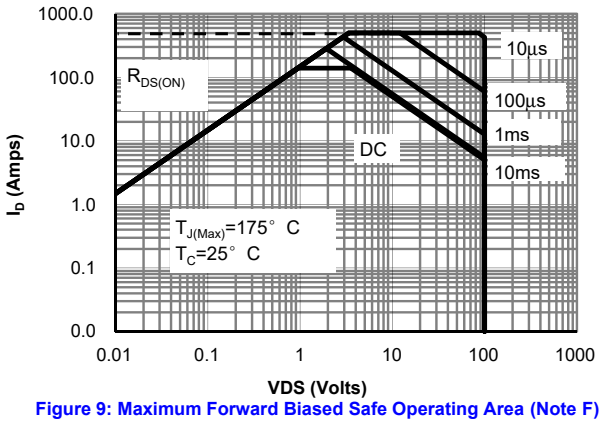


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

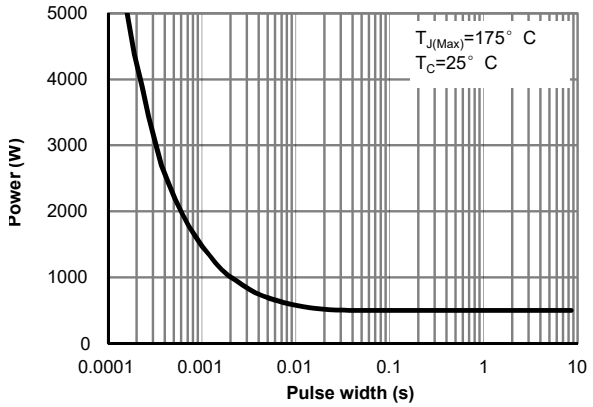


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

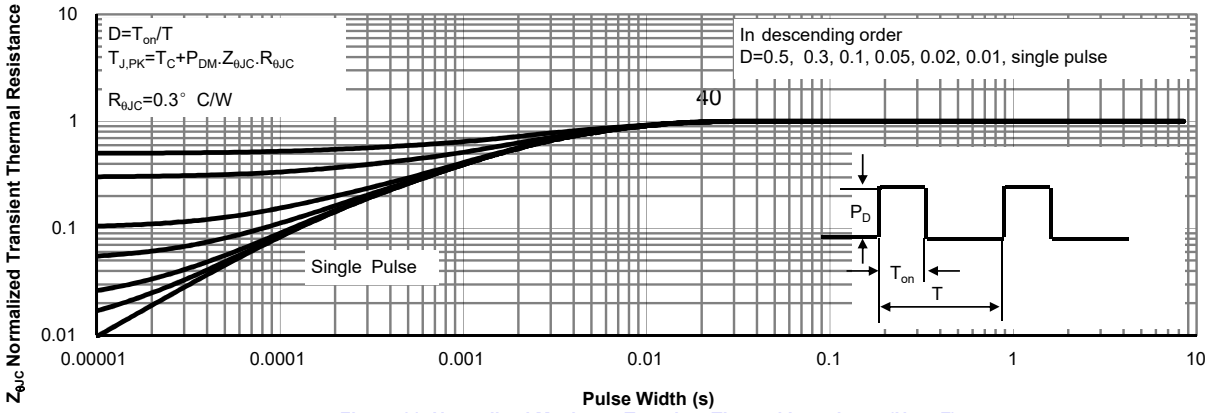


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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